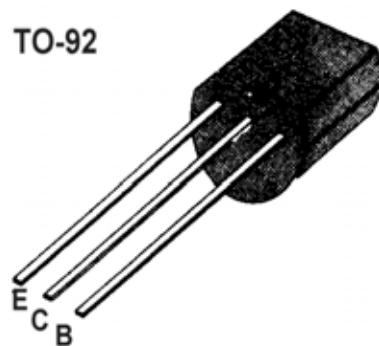


■■ APPLICATION: AF AMPLIFIER APPLICATION.

—PNP silicon—

■■ MAXIMUM RATINGS (Ta=25°C)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CBO}	-60	V
Collector-emitter voltage	V _{CEO}	-50	V
Emitter-base voltage	V _{EBO}	-7	V
Collector current	I _C	-150	mA
Collector Power Dissipation	I _{CP}	-300	mA
Junction Temperature	P _C	400	mW
Storage Temperature Range	T _J	150	°C
Storage Temperature Range	T _{stg}	-55~150	°C



■■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
Common Emitter DC Current Gain	h _{FE}	100		560		V _{CE} = -6 V, I _C = -1 mA
Collector Cut-off Current	I _{CBO}			-0.1	μA	V _{CB} = -40 V, I _E =0
Emitter Cut-off Current	I _{EBO}			-0.1	μA	V _{EB} = -6 V, I _C =0
Collector-Base Breakdown Voltage	BV _{CBO}	-60			V	I _C = -0.01 mA, I _E =0
Collector-Emitter Breakdown Voltage	BV _{CEO}	-50			V	I _C = -1 mA, I _B =0
Emitter-Base Breakdown Voltage	BV _{EBO}	-7			V	I _E = -0.01 mA, I _C =0
Collector-Emitter Saturation Voltage	V _{CE(sat)}			-0.3	V	I _C = -50 mA, I _B = -5 mA
Gain bandwidth product	f _T	80	100		MHz	I _C = -1 mA, V _{CE} = -6 V
Common Base Output Capacitance	C _{ob}		4		pF	V _{CB} = -6 V, I _E =0, f= 1 MHz

■■ h_{FE} Classification

Classification	O	S	Y	T	U
h _{FE}	100-200	140-280	200-400	280-560	